

# Graphene spaser

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We show that graphene monolayer coupled to multi-quantum well system can form a graphene spaser, which is a coherent quantum generator of surface plasmons in graphene. The active element of graphene spaser is a multi-quantum well system with a design similar to the design of an active element of quantum cascade laser. Under realistic parameters of the multi-quantum well system, the spasing in graphene monolayer can be achieved at a finite doping of graphene and at a plasmon frequency,  $\approx 0.15$  eV, close to the typical frequency of intersubband transitions in multi-quantum well systems.

Quantum nanoplasmonics becomes fast growing field of nanooptics[1] due to unique property of plasmonic system to strongly enhance the optical field within spatial subwavelength range. Such property results in many applications of nanoplasmonic systems, such as surface enhanced Raman scattering[2–4], ultrasensing[5], surface-plasmon enhanced photodetectors[6], biomedical testing[5, 7] and others. One of such applications is a spaser (Surface Plasmon Amplification by Stimulated Emission of Radiation), which is nanoplasmonic counterpart of laser. Spaser has been proposed theoretically in Ref. [8] and observed experimentally in Ref. [9]. Spaser consists of plasmonic system coupled to active (gain) medium, which results in coherent generation of surface plasmons with nanolocalized intense optical field. One of the limitations on coherent generation of surface plasmons is determined by finite damping rate of plasmon excitations.

In the present paper we propose to utilize the graphene monolayer[10–12] as a plasmonic system[13–16] of spaser. Graphene is a layer of crystalline carbon that just one atom thick. The honeycomb 2D crystalline structure of graphene results in a very unique energy dispersion law[17]. Namely, the low-energy excitations are described by chiral relativistic massless Dirac-Weyl equation. The chiral nature of electronic states in graphene results in strong suppression of electron scattering, which highly increases the mobility ( $\sim 15,000$  cm<sup>2</sup>V<sup>-1</sup>s<sup>-1</sup>) of charge carrier in graphene and strongly suppresses theoretically estimated plasmonic losses. For plasmon frequency below the interband loss threshold, which is determined by the level of graphene doping, i.e., the Fermi energy, and below the optical phonon loss threshold,  $\approx 0.2$  eV, the plasmon relaxation time can be estimated from DC measurements and is around  $\tau \approx 0.6$  ps [14], which results in low plasmon damping rate  $1/\omega\tau \approx 0.01$ .

As an active element of graphene spaser, we will consider a multi-quantum well system. The design of such system is similar to the design of an active element of quantum cascade laser. Quantum cascade lasers, proposed theoretically in 1971[18] and realized experimentally in 1994,[19, 20] utilize the intersubband optical transitions in specially designed superlattice of quantum wells to generate coherent lasing in mid-infrared and terahertz optical range.[21] Within the active region of quantum

cascade structure, optical transitions occur between subband levels of dimensional quantization in the growth direction.[22] The advantage of quantum cascade laser system over conventional semiconductor lasers, which are based on inter-band transitions, is that a single electron propagating through the cascade structure can generate as many photons as the number of active regions within quantum cascade laser. In the graphene spaser we utilize only one multi-quantum well active element of quantum cascade laser. The design of such active element is characterized by strong electrical injection of electrons into the upper subband level of multi-quantum well system and fast and efficient extraction of electrons from the lower subband level.

Our spaser system is shown schematically in Fig. 1 for one of the possible designs of active element of cascade system. Since the plasmonic modes of graphene are strongly localized in the growth direction, i.e. along axis  $z$ , with localization length  $\approx 3 - 5$  nm, only one active element of quantum cascade system is coupled to the plasmonic modes of graphene. The gain, i.e., population inversion, in multi-quantum well system is introduced through a voltage applied to the system.

To find the plasmonic modes of graphene, we assume that graphene monolayer is surrounded by two homogeneous effective media with dielectric constants  $\epsilon_1$  and  $\epsilon_2$ . Therefore we replace the cascade system with homogeneous dielectric media. Spatial distribution of electric field of plasmonic excitations in graphene and their dispersion relation are determined by solution of Maxwell's equations with corresponding boundary condition. The boundary conditions are introduced in terms of 2D current, generated in graphene layer, where the current is proportional to the in-plane electric field and is determined by graphene conductance,  $\sigma(\omega, q)$ . We consider TM plasmon mode in graphene monolayer with the distribution of electric field in the following form[14]

$$\vec{E}_q = \begin{pmatrix} E_{qz} \\ E_{qy} \end{pmatrix} = \mathcal{E}_q \begin{pmatrix} -i\frac{q}{k_{2z}} e^{iqz} e^{k_{2z}z} \\ e^{iqz} e^{k_{2z}z} \end{pmatrix} \quad (1)$$

at  $z < 0$  and

$$\vec{E}_q = \begin{pmatrix} E_{qz} \\ E_{qy} \end{pmatrix} = \mathcal{E}_q \begin{pmatrix} i\frac{q}{k_{1z}} e^{iqz} e^{-k_{1z}z} \\ e^{iqz} e^{-k_{1z}z} \end{pmatrix} \quad (2)$$

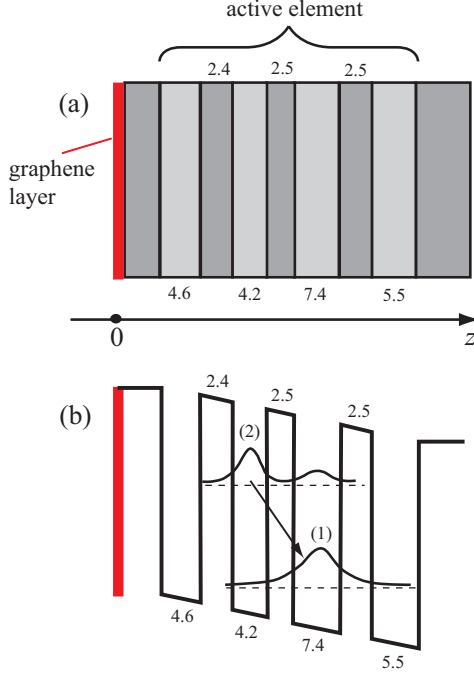


FIG. 1: (a) Schematic illustration of coupled graphene and quantum cascade laser structure. The numbers (in nm) are the well ( $\text{Ga}_{0.47}\text{In}_{0.53}\text{As}$ ) and barrier ( $\text{Al}_{0.48}\text{In}_{0.52}\text{As}$ ) widths. The wells and barriers are shown by light and dark gray colors, respectively. (b) Energy-band diagram (schematic) of the active region of a quantum cascade laser structure under constant electric field. The relative wave functions of subbands (1) and (2) as well as optical transitions corresponding to spaser action are shown schematically.

at  $z > 0$ . The corresponding profile of magnetic field is

$$H_{qx} = \mathcal{E}_q \begin{cases} \frac{i\omega\epsilon_1}{4\pi k_{1z}} e^{iqz} e^{-k_{1z}z}, & \text{at } z < 0 \\ \frac{i\omega\epsilon_2}{4\pi k_{2z}} e^{iqz} e^{k_{2z}z}, & \text{at } z > 0 \end{cases} \quad (3)$$

Here  $\mathcal{E}_q$  is the amplitude of the plasmonic mode with frequency  $\omega_q$  and wave vector  $q$ . The spatial decay of electromagnetic field away from the graphene layer is determined by wave vectors  $k_{1z}$  and  $k_{2z}$ , which are given by the following expressions

$$k_{1z}^2 = q^2 - \epsilon_1 \frac{\omega_q^2}{c^2}, \quad (4)$$

$$k_{2z}^2 = q^2 - \epsilon_2 \frac{\omega_q^2}{c^2}. \quad (5)$$

Considering the limit  $q \gg \omega/c$  and assuming the Drude expression for graphene conductance, we obtain from the boundary conditions the well-known dispersion relation for plasmons in graphene

$$q(\omega) \approx k_{1z} \approx k_{2z} \approx \frac{\hbar^2(\epsilon_1 + \epsilon_2)}{4e_0^2 E_F} \left(1 + \frac{i}{\omega_q \tau}\right) \omega_q^2, \quad (6)$$

where  $E_F$  is the Fermi energy of electrons in graphene and  $\tau$  is the relaxation time, which also determines the plasmon decay time.

Applying the second quantization approach to plasmons in graphene, we introduce electric field operator in the following form

$$\hat{\vec{E}} = \sum_q \vec{E}_q (\hat{a}_q^+ + \hat{a}_q), \quad (7)$$

where  $\hat{a}_q$  and  $\hat{a}_q^+$  are operators of creation and annihilation of a plasmon with the wave vector  $q$  and frequency  $\omega_q$ . Within the second quantization approach, the amplitude  $\mathcal{E}_q$  of plasmonic mode is determined from the condition

$$\frac{1}{8\pi} \left[ \int d\vec{r} \epsilon(r) |\vec{E}_q|^2(\vec{r}) + \int d\vec{r} H_{qx}^2(\vec{r}) \right] = \hbar\omega. \quad (8)$$

Then

$$\mathcal{E}_q = \sqrt{\frac{2\pi\hbar\omega_q q}{S_0(\epsilon_1 + \epsilon_2)}}, \quad (9)$$

where  $S_0$  is the area of graphene layer.

The Hamiltonian of a spaser, shown in Fig. 1, has the form

$$\mathcal{H} = \sum_{i=1,2} \sum_{\vec{k}} E_i(k) \hat{c}_{i,k}^+ \hat{c}_{i,k} + \hbar \sum_q \omega_q \hat{a}_q^+ \hat{a}_q + \hbar \sum_{q,k} \Omega_{12}(k, q) \left( \hat{a}_q^+ \hat{c}_{1,k}^+ \hat{c}_{2,k} + h.c. \right), \quad (10)$$

where the first sum describes the Hamiltonian of the gain medium, which consists of two subbands "1" and "2" (see Fig. 1) with energies  $E_1(k) = \epsilon_1 + \hbar^2 k^2 / 2m^*$  and  $E_2(k) = \epsilon_2 + \hbar^2 k^2 / 2m^*$ , respectively. Here  $m^*$  is an electron effective mass,  $\epsilon_1 < \epsilon_2$ , and  $k$  is a two dimensional electron wave vector. The second sum in Eq. (10) is the Hamiltonian of plasmons in graphene layer, and the last sum describes the dipole interaction of plasmons with active medium,  $\propto \hat{\vec{E}} \hat{\vec{d}}$ . Here the dipole vector  $\hat{\vec{d}}$  of the active medium has only  $z$  component. The dipole interaction strength is determined by the corresponding Rabi frequency,  $\Omega_{12}(q)$ ,

$$\Omega_{12}(\vec{k}, \vec{q}) = e_0 \mathcal{E}_q \int d\vec{r} \psi_{1,k}^*(\vec{r}) E_{q,z} \psi_{2,k}(\vec{r}), \quad (11)$$

where  $e_0$  is the electron charge,  $\psi_{1,k}$  and  $\psi_{2,k}$  are electron wave functions with wave vector  $k$  of subbands 1 and 2, respectively. Assuming that the electron dynamics in  $x$ ,  $y$ , and  $z$  directions is separable, we can express the wave functions in the following form  $\psi_{i,k} = \chi_i(z) S_0^{-1/2} \exp(i\vec{k}\vec{\rho})$ , where  $\vec{\rho} = (x, y)$  and  $i = 1, 2$ . Then expression (11) becomes

$$\Omega_{12}(\vec{k}, \vec{q}) = e_0 \mathcal{E}_q \int dz \chi_1^*(z) e^{-k_{2z}z} z \chi_2(z) \approx \mathcal{E}_q d_{12} e^{-qL}, \quad (12)$$

where  $d_{12} = \int dz \chi_1^*(z) e_0 z \chi_2(z)$  is the dipole matrix element, and  $L$  is the distance between graphene monolayer

and the maxima of the subband wave functions  $\chi_i(z)$ , which correspond to the active quantum well of cascade structure.

Introducing the density matrix of the active region of the system,  $\rho_{\vec{k}}(t)$ , we describe the dynamics of the spaser within the density matrix approach, writing the equation for the density matrix,  $i\hbar\dot{\rho}_{\vec{k}}(t) = [\rho_{\vec{k}}(t), \mathcal{H}]$ , and for occupation numbers of the plasmons. Within a stationary regime we obtain the condition of spasing in the following form[8]

$$\frac{(\gamma + \Gamma_{12})^2}{(\omega_{12} - \omega_q)^2 + (\Gamma_{12} + \gamma)^2} \sum_{\vec{k}} \left| \Omega_{12}(\vec{k}, \vec{q}) \right|^2 \geq \gamma \Gamma_{12}, \quad (13)$$

where  $\gamma = \hbar/\tau$  is the surface plasmon relaxation rate,  $\Gamma_{12}$  is the subband polarization relaxation rate, and  $\omega_{12} = (\varepsilon_2 - \varepsilon_1)/\hbar$ . Substituting expression (9) into Eq. (12), we obtain

$$\frac{(\gamma + \Gamma_{12})^2}{(\omega_{12} - \omega_q)^2 + (\Gamma_{12} + \gamma)^2} \frac{\hbar\omega_q q k_0^2}{2(\epsilon_1 + \epsilon_2)} |d_{12}|^2 e^{-2qL} \geq \gamma \Gamma_{12}. \quad (14)$$

Here the wave vector  $k_0$ , i.e., quasi-Fermi wave vector, determines the largest wave vector of the states, which are partially occupied by electrons in the active region. Only such states contribute to the sum in Eq. 13.

At the resonance, i.e. at  $\omega_{12} = \omega_q$ , the condition of spasing becomes

$$\frac{\hbar\omega_q q k_0^2}{2(\epsilon_1 + \epsilon_2)} |d_{12}|^2 e^{-2qL} \geq \gamma \Gamma_{12}. \quad (15)$$

For a given structure of the active region, expression (15) introduces a constrain on plasmon relaxation rate,  $\gamma$ . The typical parameters of the active region (corresponding, for example, to the structure shown in Fig. 1) are  $\hbar\omega_{12} = 130$  meV,  $d_{12} = 1.5e_0$  (nm $\cdot e_0$ ), and  $L \approx 16$  nm. The typical intersubband relaxation time in the quantum well cascade systems is  $\tau_{12} = \hbar/\Gamma_{12} \approx 1$  ps[23, 24]. Under resonant condition the inter-subband transition frequency  $\hbar\omega_{12} = 130$  meV, which is equal to the plasmon frequency, correspond to the plasmon wave vector  $q^{-1} \approx 30$  Å – see Eq. (6). Assuming that  $k_0 \approx 0.04$  nm $^{-1}$  and  $\epsilon_1 + \epsilon_2 = 5$ , we obtain

$$\gamma \leq 2.5 \cdot 10^{-3} \text{ eV} \quad (16)$$

with corresponding relaxation time  $\tau \geq 3 \cdot 10^{-13}$  s.

Substituting relation (6) into inequality (15), we obtain a condition on plasmon relaxation time

$$\tau \geq \tau_{\min} = \frac{8e_0^2 \Gamma_{12} E_F}{\hbar^2 \omega_q^3 k_0^2 |d_{12}|^2} e^{2qL}. \quad (17)$$

The dependence of the minimum plasmon relaxation time,  $\tau_{\min}$ , on the plasmon frequency  $\omega_q$  is shown in fig. 2(a) for different Fermi energies  $E_F$  of electrons in graphene. The data clearly show that there is a broad range of plasmon frequencies,  $\hbar\omega_q \approx 0.1 \div 0.3$  eV, at

which the minimum relaxation time is relatively small,  $\tau_{\min} \sim 0.03$  ps. Outside this range the minimum relaxation time strongly increases. The typical values of frequencies of intersubband transition in quantum well structures are within the frequency range  $0.1 \div 0.3$  eV.

The condition (17) can be also expressed in terms of dimensionless plasmon damping rate,  $\gamma = 1/(\omega_q \tau)$ ,

$$\gamma \leq \gamma_{\max} = \left( \frac{k_0^2 |d_{12}|^2}{8e_0^2} \right) \left( \frac{\hbar^2 \omega_q^2}{\Gamma_{12} E_F} \right) e^{-2qL}. \quad (18)$$

Restriction (18) on the surface plasmon damping rate depends in the plasmon frequency,  $\omega_q$ , which under resonant condition is equal to the frequency of intersubband optical transitions within the active region of cascade system. As a function of frequency  $\omega_q$ , the damping rate  $\gamma_{\max}$  has a sharp maximum, the position of which is determined by condition  $q \approx 1/2L$  or  $\omega_q \approx (2e_0^2 E_F / [L\hbar^2(\epsilon_1 + \epsilon_2)])^{1/2}$ , and depends on parameters of the system, such as the Fermi energy,  $E_F$ , of electrons in graphene and the distance  $L$  between the graphene monolayer and the active quantum well of cascade structure. The dependence of the plasmon damping rate  $\gamma_{\max}$  on the frequency of surface plasmons,  $\omega_q$ , is shown in Fig. 2(b) for different values of the Fermi energy  $E_F$ . The maximum value of  $\gamma_{\max}$  is  $k_0^2 |d_{12}|^2 / [4e\Gamma_{12}(\epsilon_1 + \epsilon_2)] \approx 0.2$  and does not depend on the Fermi energy. The Fermi energy affects only the position of the maximum.

Below the frequency of optical phonons in graphene monolayer, which is  $\sim 0.2$  eV, and below the Fermi frequency, which determines interband loss threshold, the relaxation time of surface plasmons in graphene can be estimated from the DC conductance of graphene. Such estimations show that the plasmon relaxation time in graphene is  $\sim 0.6$  ps, which corresponds to the plasmon damping rate  $\gamma \approx 0.01$  at frequency  $\hbar\omega_q = 130$  meV. Such plasmon damping rate is well below  $\gamma_{\max}$  for a broad range of frequencies  $\omega_q$  – see Fig. 2(b).

In Ref. 16 the plasmon damping rate  $\gamma = 1/(\omega_q \tau)$  in graphene has been measured experimentally by infrared nano-imaging method. The best fitting to experimental data has been obtained for strong damping  $\gamma = 0.135$  at plasma frequency  $\hbar\omega_q = 0.11$  eV, which corresponds to the plasmon relaxation time  $\tau = 0.044$  ps. Even at such strong plasmon damping, the plasmon damping rate  $\gamma = 0.135$  ps is less than the maximum rate  $\gamma_{\max} \sim 0.2$  – see Fig. 2(b). Taking into account that plasmon relaxation rate strongly increases above optical phonon loss threshold, which is  $\approx 0.2$  eV, we can conclude that the optimal Fermi energy in graphene should be around 0.5 eV. For such Fermi energy the maximum of  $\gamma_{\max}$  is realized at plasmon frequency  $\hbar\omega_q \approx 0.15$  eV – see Fig. 2(b). The above results clearly suggests that the spasing can be realized in realistic graphene systems coupled to quantum well structures.

In conclusion, the graphene monolayer deposited on a top of specially designed stack of quantum wells forms a spaser, which is a coherent source of surface plasmons

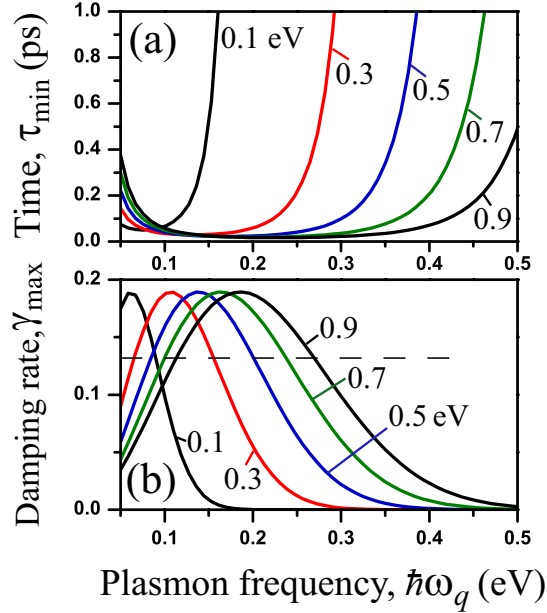


FIG. 2: (a) Minimum relaxation time, defined by Eq. (17), of plasmons in graphene is shown as a function of resonant plasmon frequency for different Fermi energies of electrons in graphene. The spasing is realized at plasmon relaxation time  $\tau > \tau_{min}$ . (b) Plasmon damping rate  $\gamma_{max}$ , defined by Eq. (18), is shown as a function of the plasmon frequency  $\omega_q$ . The dashed line shows the experimental value of plasmon damping rate  $\gamma \approx 0.135$  [16]. The numbers next to the lines in (a) and (b) are the Fermi energies in eV.

in graphene. The system of quantum wells is designed similar to an active element of quantum cascade laser and is characterized by strong electrical injection of electrons into the upper subband level of multi-quantum well system and fast and efficient extraction of electrons from the lower subband level. Under realistic parameters of the multiple quantum wells, our analysis show that the condition of spasing, i.e., coherent generation of plasmons in graphene, can be achieved at finite doping of graphene monolayer, which corresponds to electron Fermi energy in graphene around 0.5 eV. The above analysis can be applied not only for graphene monolayer, but also for graphene-based nanoscale structures such as graphene nanoribbons and graphene quantum dots.

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